

2N6426



NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CEO}	Collector-Emitter Voltage	40	V	
V _{CBO}	Collector-Base Voltage	40	V	
V _{EBO}	Emitter-Base Voltage	12	V	
Ic	Collector Current - Continuous 1		A	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

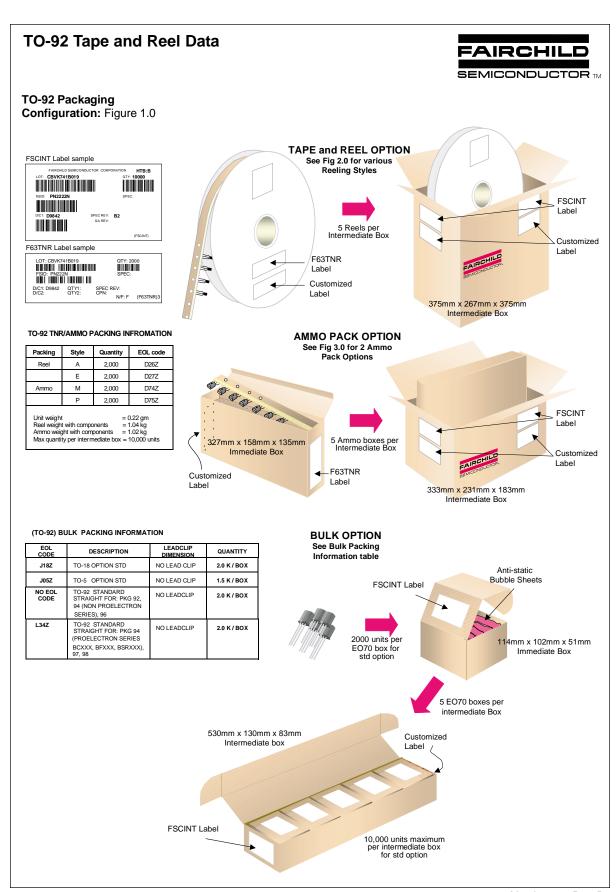
Symbol	Characteristic	Max	Units
		2N6426	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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NPN Darlington Transistor (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	12		V
СВО	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		50	nA
CEO	Collector Cutoff Current	$V_{CE} = 25 \text{ V}, I_{B} = 0$		1.0	μΑ
ЕВО	Emitter Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		50	nA
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$V_{CE} = 5.0 \text{ V}, I_C = 500 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 0.5 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 0.5 \text{ mA}$	20,000	200,000 1.2 1.5	V
VCE(Sat)	Composed Emiliar Catalian Contage				
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}$		1.75	V
SMALL S	SIGNAL CHARACTERISTICS Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz		7.0	pF
C _{ib}	Input Capacitance	$V_{EB} = 1.0 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz}$		15	pF
h _{fe}	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0 kHz	20,000		•
h _{ie}	Input Impedance	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	100	2,000	kΩ
h _{oe}	Output Admittance	f = 1.0 kHz		1,000	μmho
NF	Noise Figure	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $R_S = 100 \text{ k}\Omega,$ $f = 10 \text{ kHz to } 15.7 \text{ kHz}$		10	dB

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

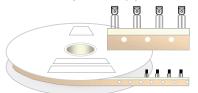


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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



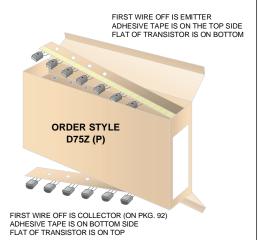
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

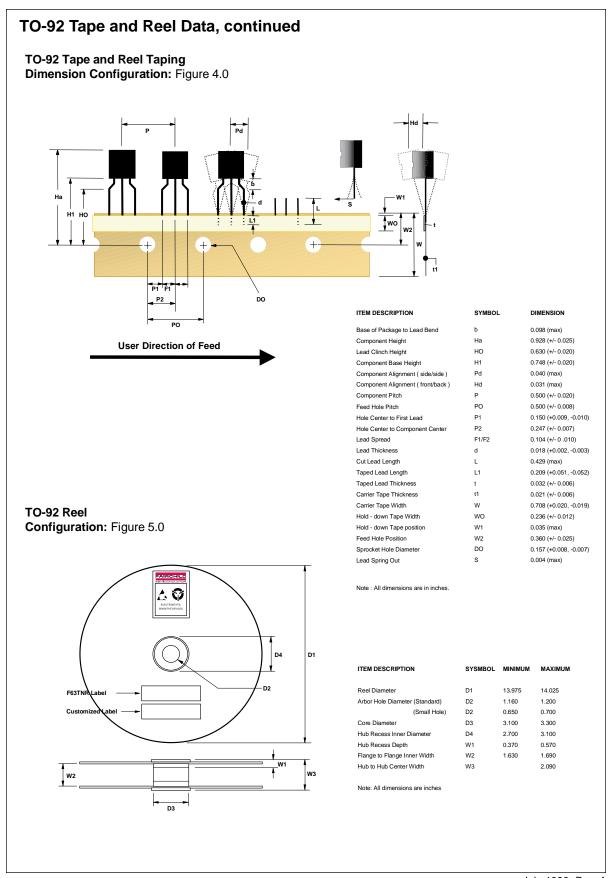
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





September 1999, Rev. B



TO-92 Package Dimensions FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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0.095 0.084 2.13

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